

Substitute for Form 1449 A & B/PTO

**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

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Complete if Known

Application Number	09/986,332
Confirmation Number	5542
Filing Date	November 8, 2001
First Named Inventor	KIYOKU, HIROYUKI
Art Unit	1765
Examiner Name	Anderson, Matthew A.
Attorney Docket Number	Q66212

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Document Number		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document
		Number	Kind Code ² (if known)		
MAA		US 5,620,557	A	04-15-1997	Katsuhide MANABE et al.
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Examiner Initials*	Cite No. ¹	Foreign Patent Document			Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Translation ⁶
		Country Code ³	Number ⁴	Kind Code ² (if known)			
MAA		JP	7-165498		06-27-1995	Toyoda Gosei Co. LTD.	Abstract + JPO Translation
MAA		JP	7-202265		08-04-1995	Mitsubishi Cable Ind. LTD.	Abstract + JPO Translation + US 5620557

NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city, and/or country where published.	Translation ⁶

Examiner Signature

Matthew Anderson

Date Considered

6/7/04

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¹ Applicant's unique citation designation number (optional). ² See Kind Codes of USPTO Patent Documents at www.uspto.gov, MPEP 901.04 or in the comment box of this document. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST. 3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to indicate here if English language Translation is attached.

Form PTO-1449 (Rev. 2-32)		U.S. Department of Commerce Patent & Trademark Office		Atty. Docket No. Q66212		Serial No.: Confirmation No.: To be Assigned	
INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)				Applicant: Hiroyuki KIYOKU, et al.			
				Filing Date: 11/8/2001		Group: 1765	

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<i>NMA</i>	International Search Report, PCT/US99/04346, June 9, 1999
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EXAMINER: <i>Matthew C. Miller</i>	DATE CONSIDERED: 6/08/04
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